<u>Standard specifications of</u> 100 mm Sn-doped β-Ga₂O₃ (001) substrate

Items		Specifications	
Orientation		(001)	
Do	opant	Sn	
Conductivity		n-type	
Resistivity (Ω·cm)		0.007-0.042	
Dim	Diameter (mm)	100 ± 0.5	
	Orientation flat width (mm)	32.5 ±2.5	
Dimensions	Index flat width (mm)	18.0 ±2.5	
ร	Thickness (mm)	kness (mm) 0.65 ±0.02	
	Reference	Fig. 1	
Offset angle		[010]:0 ±1	
(d	egree)		
F۷	VHM	[010]:50 or less	
(arcsec)		[100]:50 or less	
Surface	Front	СМР	
ace	Back	СМР	

Remarks

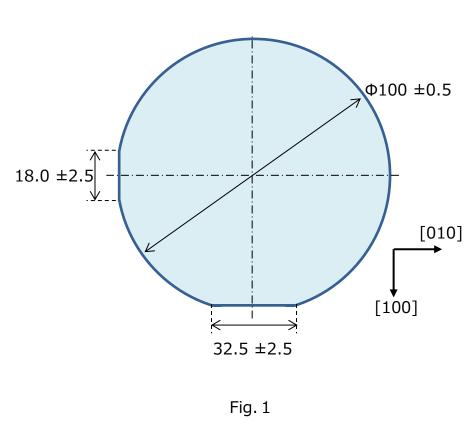
 $1\ {\rm There}\ {\rm are}\ {\rm cases}\ {\rm in}\ {\rm which}\ {\rm the}\ {\rm opposite}\ {\rm side}\ {\rm of}\ {\rm OF}\ {\rm is}\ {\rm chipped}\ {\rm less}\ {\rm than}\ 18\ {\rm mm}.$

2 There are cases in which the OF side is chipped less than 32.5 mm ± 2.5 mm.

3 These products must be used for research and development purposes only.

4 The substrates must not be used as a seed crystal.

5 The specifications are subject to change without notice.





Novel Crystal Technology, Inc. 2024.12.18

<u>Standard specifications of</u> <u>2 inch Sn-doped β-Ga₂O₃ (001) substrate</u>

Items		Specifications	
Orientation		(001)	
Dopant		Sn	
Conductivity		n-type	
Resistivity (Ω·cm)		0.007-0.042	
Dimensions	Diameter (mm)	50.8 ±0.3	
	Orientation flat width (mm)	15.9 ± 2.5	
	Index flat width (mm)	8.0 ±2.5	
	Thickness (mm)	0.65 ± 0.02	
	Reference	Fig. 2	
Offset angle (degree)		[010]:0 ±1	
		[100]:0 ±1	
FWHM (arcsec)		[010]:50 or less	
		[100]:50 or less	
Surface	Front	СМР	
ace	Back	СМР	

Remarks

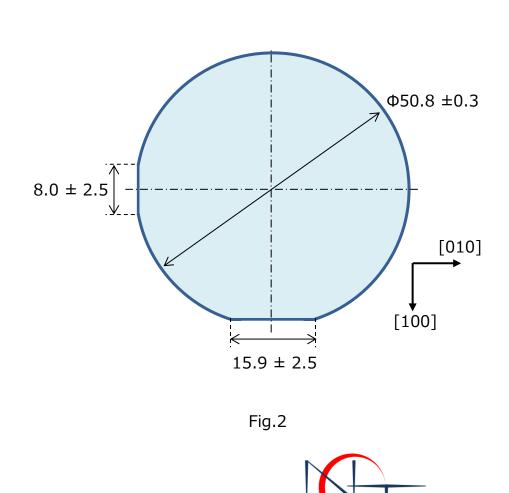
 $1\ \mbox{There}\ \mbox{are}\ \mbox{cases}\ \mbox{in which the opposite side of OF}\ \mbox{is chipped less than 8 mm}.$

2 There are cases in which the OF side is chipped less than 15.9 mm ± 2.5 mm.

3 These products must be used for research and development purposes only.

4 The substrates must not be used as a seed crystal.

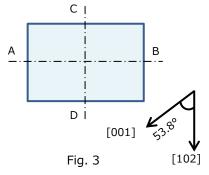
5 The specifications are subject to change without notice.



Novel Crystal Technology, Inc.

Standard specifications of 10×15 mm² β-Ga₂O₃ (010) substrates

Items		Specifications			
Orientation		(010)			
Dopant		Sn	Undoped	Fe	
Conductivity		n-type	n-type	Insulating $(>10^{10}\Omega \cdot cm)$	
Nd-Na (cm ⁻³)		$1 \times 10^{18} - 9 \times 10^{18}$	≦9×10 ¹⁷	-	
D	A-B (mm)	15 ±0.3	15 ±0.3	15 ±0.3	
Dimensions	C-D (mm)	10 ±0.3	10 ±0.3	10 ±0.3	
nsio	Thickness (mm)	0.5 ± 0.02	0.5 ± 0.02	0.5 ±0.02	
ns	Reference	Fig. 3	Fig. 3	Fig. 3	
Of	fset angle	⊥[102]:0 ±1	⊥[102]:0 ±1	⊥[102]:0 ±1	
(degree)		[102]:0 ±1	[102]:0 ±1	[102]:0 ±1	
FWHM (arcsec)		⊥[102]:150 or less	⊥[102]:150 or less	⊥[102]:150 or less	
IV	arcsec)	[102]:150 or less	[102]:150 or less	[102]:150 or less	
Surface	Front	СМР	СМР	СМР	
ace	Back	Grinding	Grinding	Grinding	



Remarks

1 These products must be used for research and development purposes only.

2 The substrates must not be used as a seed crystal.

3 The specifications are subject to change without notice.

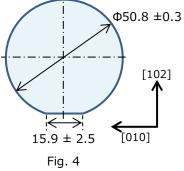
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Standard specifications of 2 inch β -Ga₂O₃ (201) substrates

Notification of discontinued products

2-inch ($\overline{2}01$) substrates are scheduled to be discontinued. Last time buy PO (non-cancelable): by Mar. 31. 2025.

Items		Specifications			
Orientation		(201)			
Dopant		Sn	Undoped	Fe	
Conductivity		n-type	n-type	Insulating $(>10^{10}\Omega \cdot cm)$	
Nd-Na (cm ⁻³)		1×10 ¹⁸ -2×10 ¹⁹	≦9×10 ¹⁷	-	
Dimensions	Diameter (mm)	50.8 ±0.3	50.8 ±0.3	50.8 ±0.3	
	Orientation flat width (mm)	15.9 ±2.5	15.9 ±2.5	15.9 ±2.5	
sion	Thickness (mm)	0.68 ± 0.02	0.68 ± 0.02	0.68 ± 0.02	
SI	Reference	Fig. 4	Fig. 4	Fig. 4	
Offset angle (degree)		[010]: 0 ±0.4	[010]: 0 ±0.4	[010]:0 ±1	
		[102]:-0.7 ±0.4	[102]:-0.7 ±0.4	[102]:-0.7 ±1	
FWHM (arcsec)		[010]:150 or less	[010]:150 or less	[010]:150 or less	
		[102]:150 or less	[102]:150 or less	[102]:150 or less	
Sur	Front	CMP	CMP	СМР	
Surface	Back	Grinding	Grinding	Grinding	



Remarks

1 There are cases in which the opposite side of OF is chipped less than 8 mm.

2 There are cases in which the OF side is chipped less than 15.9 mm ± 2.5 mm.

3 These products must be used for research and development purposes only.

4 The substrates must not be used as a seed crystal.

5 The specifications are subject to change without notice.

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